



2SB1260

PNP SILICON TRANSISTOR

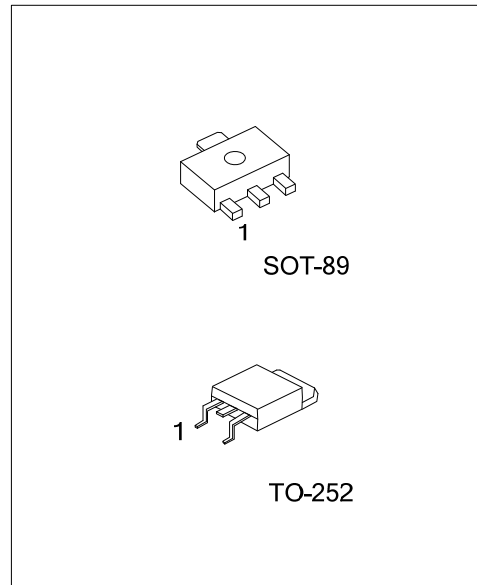
POWER TRANSISTOR

■ DESCRIPTION

The UTC **2SB1260** is a epitaxial planar type PNP silicon transistor.

■ FEATURES

- * High breakdown voltage and high current.
 $BV_{CEO} = -80V, I_C = -1A$
- * Good h_{FE} linearity.
- * Low $V_{CE(SAT)}$



■ ORDERING INFORMATION

Ordering Number	Package	Pin Assignment			Packing
		1	2	3	
2SB1260G-x-AB3-R	SOT-89	B	C	E	Tape Reel
2SB1260G-x-TN3-R	TO-252	B	C	E	Tape Reel

Note: Pin Assignment: B: Base C: Collector E: Emitter

<p>2SB1260G-x-AB3-R</p>	<p>(1) R: Tape Reel (2) AB3: SOT-89, TN3: TO-252 (3) refer to Classification of h_{FE} (4) G: Halogen Free and Lead Free, L: Lead Free</p>
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■ MARKING

SOT-89	TO-252

■ ABSOLUTE MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector -Base Voltage	V_{CBO}	-80	V
Collector -Emitter Voltage	V_{CEO}	-80	V
Emitter -Base Voltage	V_{EBO}	-5	V
Peak Collector Current (single pulse, $P_w=100\text{ms}$)	I_{CM}	-2	A
DC Collector Current	I_C	-1	A
Power Dissipation	SOT-89	0.5	W
	TO-252	1.9	W
Junction Temperature	T_J	+150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-40 ~ +150	$^{\circ}\text{C}$

Note 1. Printed circuit board, 1.7mm thick, collector copper plating 100mm² or larger.

2. Absolute maximum ratings are those values beyond which the device could be permanently damaged.
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

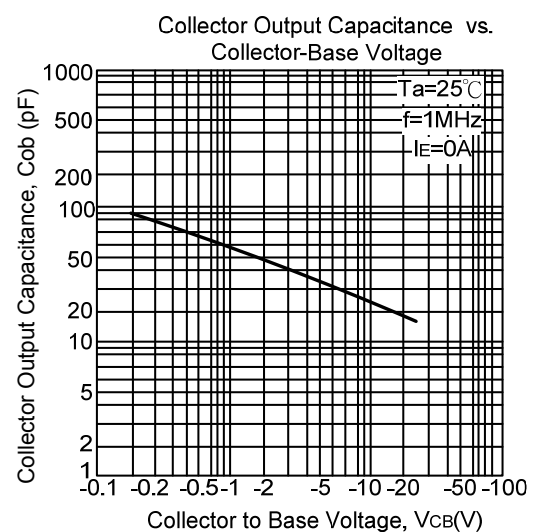
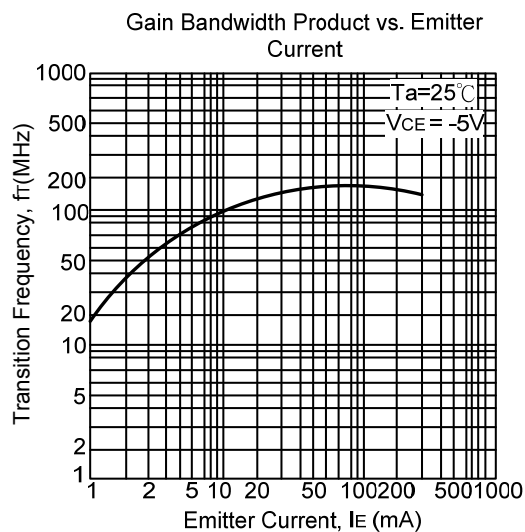
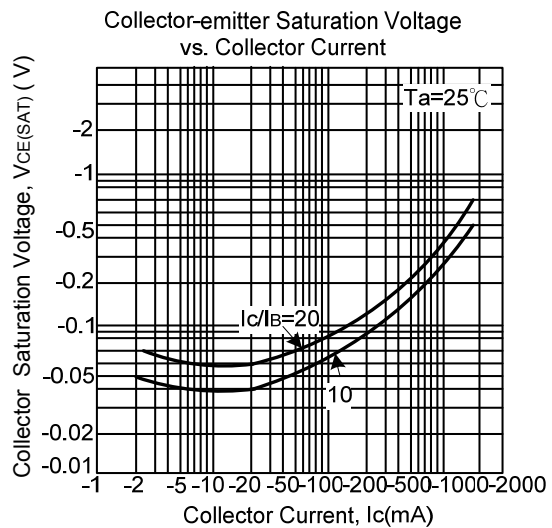
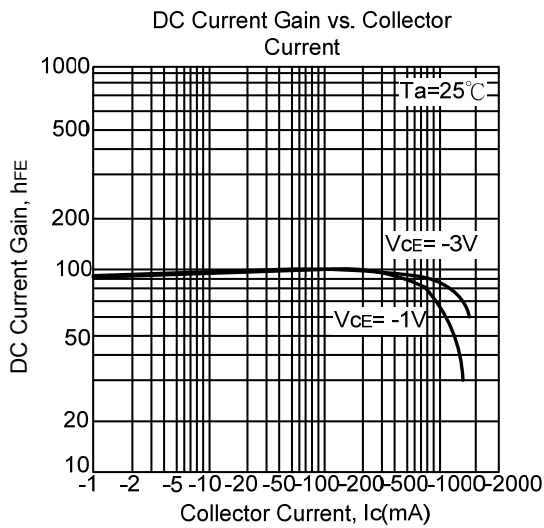
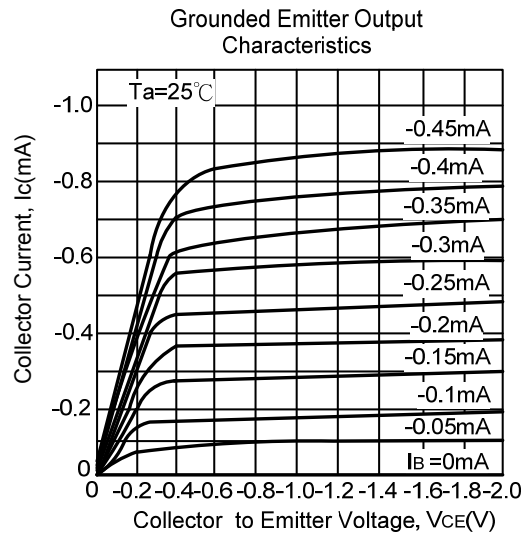
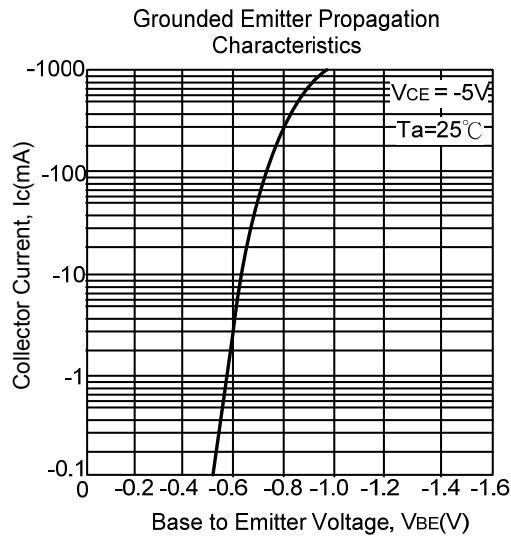
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Base Breakdown Voltage	BV_{CBO}	$I_C = -50\mu\text{A}$	-80			V
Collector Emitter Breakdown Voltage	BV_{CEO}	$I_C = -1\text{mA}$	-80			V
Emitter Base Breakdown Voltage	BV_{EBO}	$I_E = -50\mu\text{A}$	-5			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -60\text{V}$			-1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB} = -4\text{V}$			-1	μA
DC Current Gain(Note 1)	h_{FE}	$V_{CE} = -3\text{V}$, $I_{OUT} = -0.1\text{A}$	82		390	
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = -500\text{mA}$, $I_B = -50\text{mA}$			-0.4	V
Transition Frequency	f_T	$V_{CE} = -5\text{V}$, $I_E = 50\text{mA}$, $f = 30\text{MHz}$		100		MHz
Output Capacitance	C_{ob}	$V_{CB} = -10\text{V}$, $I_E = 0$, $f = 1\text{MHz}$		25		pF

Note 1: Pulse test: $P_w < 300\mu\text{s}$, Duty Cycle $< 2\%$

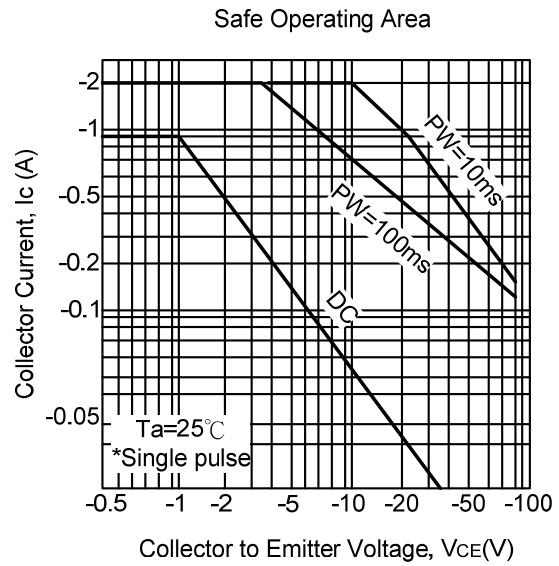
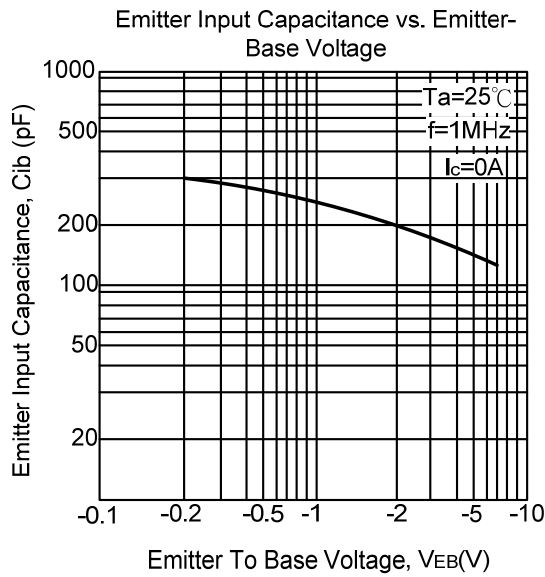
■ CLASSIFICATION OF h_{FE}

RANK	P	Q	R
RANGE	82 ~ 180	120 ~ 270	180 ~ 390

TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS(Cont.)



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